

Silicon NPN Power Transistors

2SC4747

**DESCRIPTION**

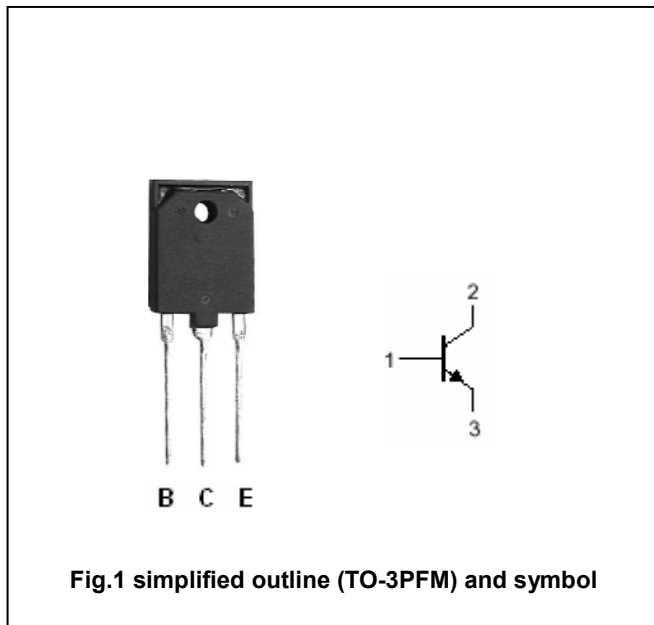
- With TO-3PFM package
- High speed switching
- High breakdown voltage

**APPLICATIONS**

- Character display horizontal deflection output applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



**Absolute maximum ratings(Ta=□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	800	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	6	V
I <sub>C</sub>	Collector current		10	A
I <sub>C(surge)</sub>	Collector current-surge		20	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25□	50	W
T <sub>j</sub>	Junction temperature		150	□
T <sub>stg</sub>	Storage temperature		-55~150	□

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA ; R <sub>BE</sub> =0	800			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =10mA ; I <sub>C</sub> =0	6			V
I <sub>CES</sub>	Collector cut-off current	V <sub>CE</sub> =1500V; R <sub>BE</sub> =0			0.5	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	8		30	
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =8A ; I <sub>B</sub> =1.6A			5	V
V <sub>BE(sat)</sub>	Base-emitter saturation voltage	I <sub>C</sub> =8A ; I <sub>B</sub> =1.6A			1.5	V
t <sub>f</sub>	Fall time	I <sub>CP</sub> =7A; I <sub>B1</sub> =1.4A			0.3	μs



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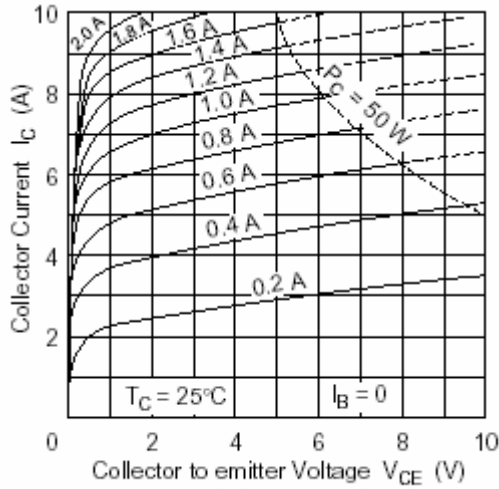


Fig.3 Static Characteristic

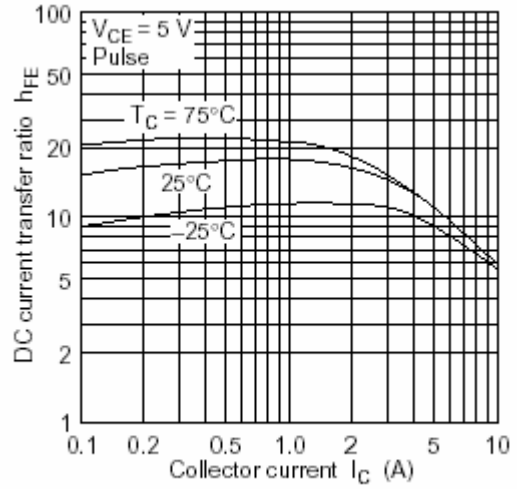


Fig.4 DC current Gain

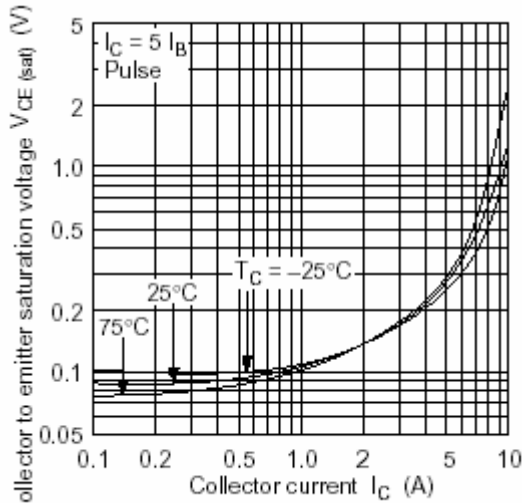


Fig.5 Collector-Emitter Saturation Voltage

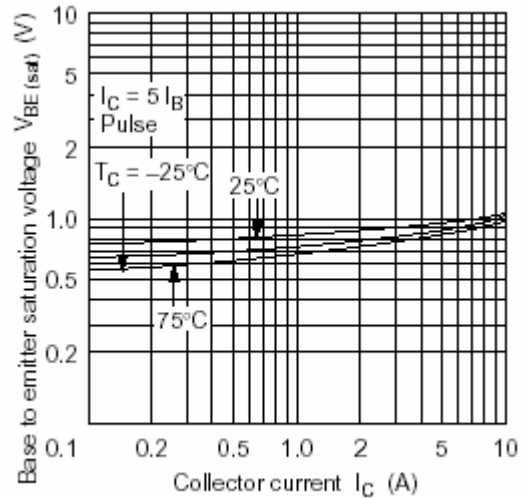


Fig.6 Base-Emitter Saturation Voltage

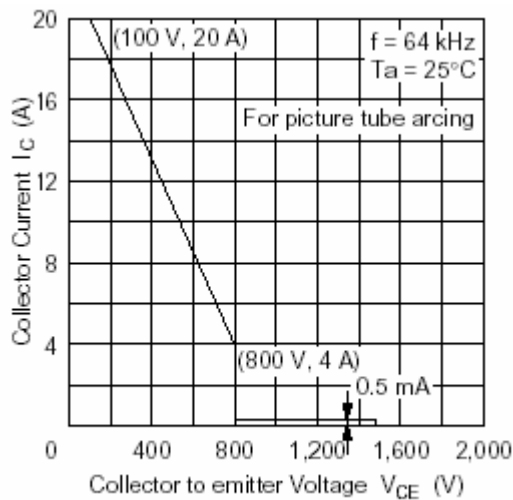


Fig.7 Safe Operating Area